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SHOWA DENKO K.K., 1-1, Ohnodai 1-chome, Midoriku, Chiba-shi, Chiba 267-0056 (JP).

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(74) Agents: AOKI, Atsushi et al.; A. AOKI, ISHIDA & ASSOCIATES, Toranomon 37 Mori Bldg., 5-1, Toranomon 3-chome, Minato-ku, Tokyo 105-8423 (JP).

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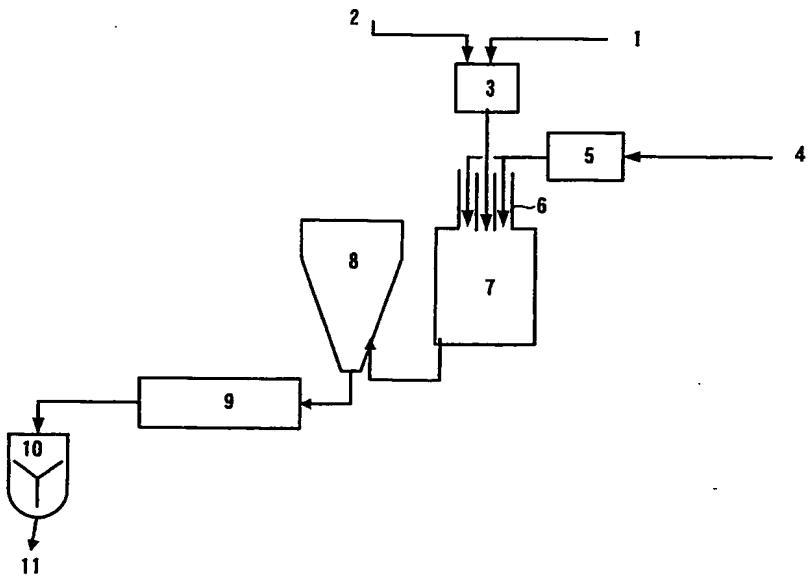
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(54) Title: PRODUCTION PROCESS OF TITANIA-SILICA MIXED CRYSTAL PARTICLES HAVING A HIGH BULK DENSITY, TITANIA-SILICA MIXED CRYSTAL PARTICLES OBTAINED BY THE PROCESS AND USES THEREOF



(57) Abstract: A process for producing titania-silica mixed crystal particles having a high bulk density and comprising titanium oxide as the main component and silicon oxide as a subsidiary component, the process comprising decomposing a gaseous titanium halide and a gaseous silicon halide, each heated at 600°C, or more in the presence of oxygen or water vapor heated at 600°C or more, heating the obtained powder at 300 to 600°C to decrease the concentration of raw material-originated hydrogen halide in the powder to 1 mass% or less, and then subjecting the powder to a treatment of dissociating the aggregated or steric structure.

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